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Jayant Baliga is an internationally recognized expert on power semiconductor devices. He is a Member of the National Academy of Engineering and a Fellow of the IEEE. He spent 15 years at the General Electric Research and Development Center, Schenectady, NY, leading their power device effort and was bestowed the highest scientific rank of Coolidge Fellow.

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Trends in Power Semiconductor Devices B. Jayant Baliga, Fellow, IEEE (Invited Paper) Abstract-This paper reviews recent trends in power semicon- ductor device technology that are leading to improvements in power losses for power electronic

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Bantval Jayant Baliga is an Indian electrical engineer best known for his work in power semiconductor devices, and particularly the invention of the insulated gate bipolar transistor. Dr. B. Jayant Baliga wrote: "Power semiconductor devices are recognized as a key component of all power electronic systems. It is estimated that at least 50 percent of the electricity used in the world is controlled by power devices. With the wide spread use of electronics in the consumer, industrial, medical, and

B. Jayant Baliga - Wikipedia

Jayant Baliga is an internationally recognized expert on power semiconductor devices. He is a Member of the National Academy of Engineering and a Fellow of the IEEE. He spent 15 years at the General Electric Research and Development Center, Schenectady, NY, leading their power device effort and was bestowed the highest scientific rank of Coolidge Fellow.

Fundamentals of Power Semiconductor Devices | B. Jayant ...

Although many universities are offering courses at the graduate level on power devices, the lack of a suitable textbook on this topic has been a hinderance. Two earlier books, Semiconductor Power Devices by S.K. Ghandhi and Modern Power Devices by B.J. Baliga, are out of print.

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Prof. Baliga is an internationally recognized expert on power semiconductor devices. He is a Member of the National Academy of Engineering and a Fellow of the IEEE. He spent 15 years at the General Electric Research and Development Center, Schenectady, NY, leading their power device effort and was bestowed the highest scientific rank of Coolidge Fellow.

Jay Baliga • Electrical and Computer Engineering

Fundamentals of Power Semiconductor Devices | B. Jayant Baliga | Springer. Numerical simulation examples to elucidate the operating physics and validate the models. Device performance attributes that allow practicing engineers in the industry to develop products. Treatment of all types of power ...

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Power semiconductor device figure of merit for high-frequency applications. Abstract: A figure of merit (the Baliga high-frequency figure of merit) is derived for power semiconductor devices operating in high-frequency circuits. Using this figure of merit, it is predicted that the power losses incurred in the power device will increase as the square root of the operating frequency and approximately in proportion to the output power.

Power semiconductor device figure of merit for high ...

Power Semiconductor. 45s. Device Figure of Merit for High-Frequency Applications. B. JAYANT BALIGA, FELLOW, IEEE. A bstract-Power devices based upon silicon technology are rapidly approaching their theoretical limits of performance. Consequently, it will be necessary to develop devices from other materials in the future in order to reduce power losses in bigb-frequency systems and in order to

acbeive high efficiencies.

Power semiconductor device figure of merit for high ...

Trends in Power Semiconductor Devices B. Jayant Baliga, Fellow, IEEE (Invited Paper) Abstract-This paper reviews recent trends in power semicon- ductor device technology that are leading to improvements in power losses for power electronic systems.

Trends in Power Semiconductor Devices - Electron Devices ...

B. JAYANT BALIGA, Ph.D., FIEEE, NAE Member Distinguished University Professor of Electrical Engineering ... "Role of Power Semiconductor Devices in Creating a Sustainable Society", Invited Plenary Paper, IEEE Applied Power Electronics Conference (APEC), Long Beach, CA, March 18, 2013 – attendance of 3800 ...

B. JAYANT BALIGA, Ph.D., FIEEE, NAE Member

Fundamentals of Power Semiconductor Devices. B. Jayant Baliga. This textbook provides an in-depth treatment of the physics of power semiconductor devices that are commonly used by the power electronics industry. Drawing upon decades of industry and teaching experience and using numerous examples and illustrative applications, the author discusses in detail the various device performance attributes that allow practicing engineers to develop energy-efficient products.

Fundamentals of Power Semiconductor Devices | B. Jayant ...

Following the introduction of power thyristors in the 1950s, many bipolar power devices were introduced with improved electrical characteristics during the next 20 years. Among these, the power bipolar transistor was the key to extending the operating frequency of power systems above 1 kHz.

B. Jayant Baliga Power Semiconductor Devices for Variable ...

An insulated-gate bipolar transistor (IGBT) is a three-terminal power semiconductor device primarily used as an electronic switch which, as it was developed, came to combine high efficiency and fast switching. It consists of four alternating layers (P-N-P-N) that are controlled by a metal–oxide–semiconductor (MOS) gate structure without regenerative [clarification needed] action.

Insulated-gate bipolar transistor - Wikipedia

PRESiCE: SiC Power Device Manufacturing Technology ... On Power Semiconductor Devices and ICs , Paper SiC -P9, pp. 375-378, June 2017, Sapporo, Japan. 12 ... W. Sung and B.J. Baliga, "On Developing One -Chip Integration of 1.2 kV SiC MOSFET and JBS Diode (JBSFET)", IEEE Transactions on Industrial Electronics , Vol. 64, pp.

8206 -8212, 2017. ...

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This invention generally relates to power semiconductor devices, and in particular to improved thyristor devices and circuits. The techniques we describe are particularly useful for so-called MOS-gated thyristors. We describe a thyristor comprising a plurality of power thyristor devices connected in parallel, each said thyristor device being operable at a device current which the device has an ...

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Wide Bandgap Semiconductor Power Devices: Materials, Physics, Design and Applications provides readers with a single resource on why these devices are superior to existing silicon devices. The book lays the groundwork for an understanding of an array of applications and anticipated benefits in energy savings.

Wide Bandgap Semiconductor Power Devices - 1st Edition

Power devices Baliga, B. J. In Modern semiconductor device physics (pp. 183–252). New York: Wiley.